

MBR1045MFS, NRVB1045MFS

Switch Mode Power Rectifiers

These state-of-the-art devices have the following features:

Features

- Low Power Loss / High Efficiency
- New Package Provides Capability of Inspection and Probe After Board Mounting
- Guardring for Stress Protection
- Low Forward Voltage Drop
- 150°C Operating Junction Temperature
- Wettable Flacks Option Available
- NRVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free and Halide-Free Devices

Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in.
- Lead Finish: 100% Matte Sn (Tin)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL 1 Requirements

Applications

- Excellent Alternative to DPAK in Space-Constrained Automotive Applications
- Output Rectification in Compact Portable Consumer Applications
- Freewheeling Diode used with Inductive Loads

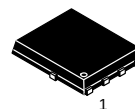


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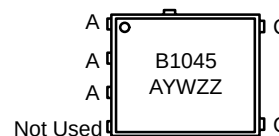
SCHOTTKY BARRIER RECTIFIERS 10 AMPERES 45 VOLTS

1,2,3  5,6



SO-8 FLAT LEAD
CASE 488AA
STYLE 2

MARKING DIAGRAM



B1045 = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
MBR1045MFST1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel
MBR1045MFST3G	SO-8 FL (Pb-Free)	5000 / Tape & Reel
NRVB1045MFST1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel
NRVB1045MFST3G	SO-8 FL (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	45	V
Average Rectified Forward Current (Rated V_R , $T_C = 142^\circ\text{C}$)	$I_{F(AV)}$	10	A
Peak Repetitive Forward Current, (Rated V_R , Square Wave, 20 kHz, $T_C = 140^\circ\text{C}$)	I_{FRM}	20	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	150	A
Storage Temperature Range	T_{stg}	-65 to +175	$^\circ\text{C}$
Operating Junction Temperature	T_J	-55 to +150	$^\circ\text{C}$
Unclamped Inductive Switching Energy (10 mH Inductor, Non-repetitive)	E_{AS}	150	mJ
ESD Rating (Human Body Model)		3B	
ESD Rating (Machine Model)		M4	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

NOTE: The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dPD/dT_J < 1/R_{JA}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Thermal Resistance, Junction-to-Case, Steady State (Assumes 600 mm ² 1 oz. copper bond pad, on a FR4 board)	$R_{\theta JC}$	–	1.7	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS

Instantaneous Forward Voltage (Note 1) ($i_F = 10\text{ A}$, $T_J = 125^\circ\text{C}$) ($i_F = 10\text{ A}$, $T_J = 25^\circ\text{C}$) ($i_F = 20\text{ A}$, $T_J = 125^\circ\text{C}$) ($i_F = 20\text{ A}$, $T_J = 25^\circ\text{C}$)	V_F	0.430 0.504 0.550 0.595	0.52 0.62 0.65 0.75	V
Reverse Current (Note 1) (Rated dc Voltage, $T_J = 125^\circ\text{C}$) (Rated dc Voltage, $T_J = 25^\circ\text{C}$)	i_R	47 0.076	170 0.500	mA
Diode Capacitance	C_D	300		pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

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TYPICAL CHARACTERISTICS

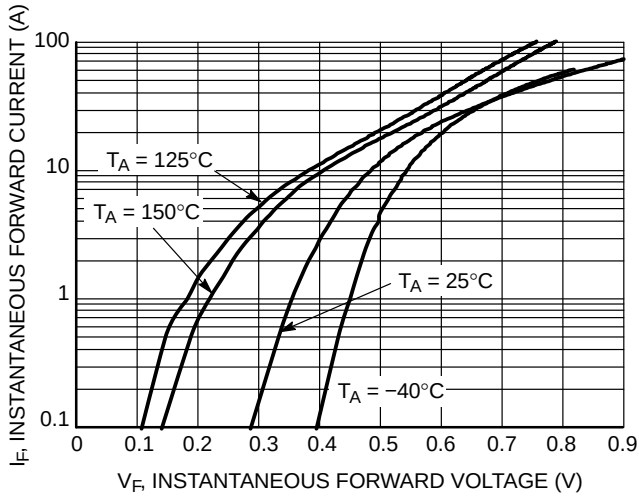


Figure 1. Typical Instantaneous Forward Characteristics

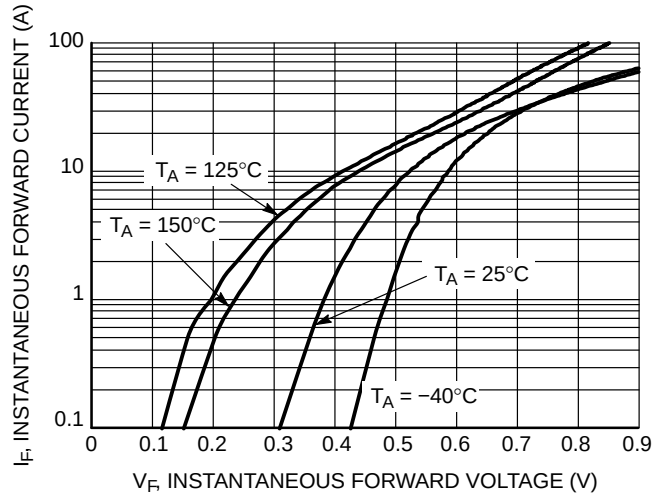


Figure 2. Maximum Instantaneous Forward Characteristics

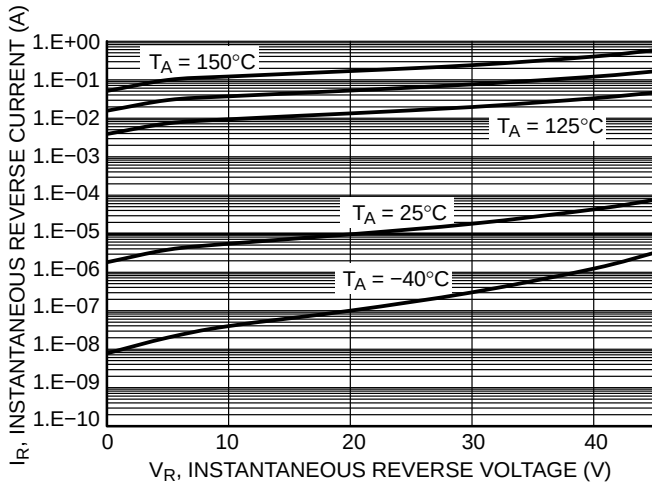


Figure 3. Typical Reverse Characteristics

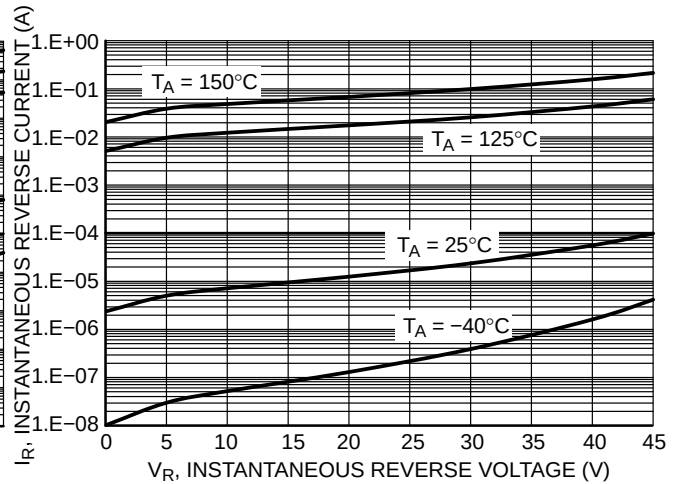


Figure 4. Maximum Reverse Characteristics

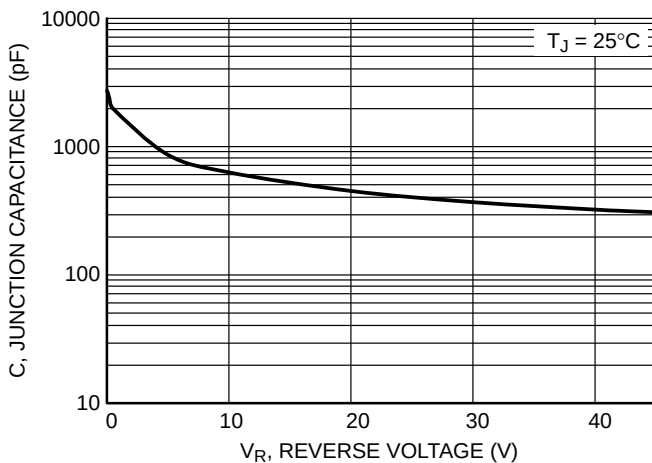


Figure 5. Typical Junction Characteristics

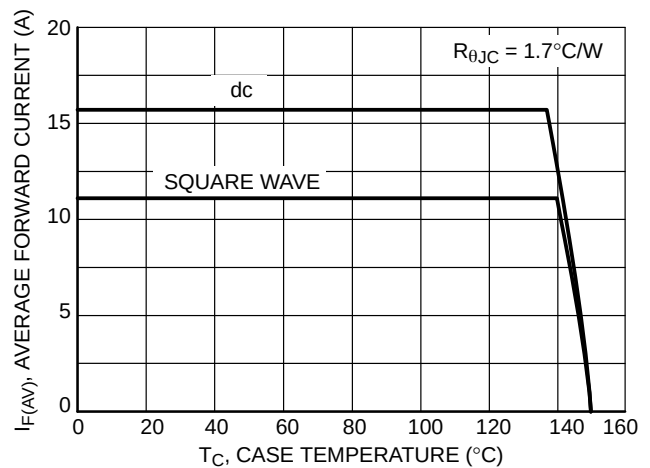


Figure 6. Current Derating TO-220AB

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TYPICAL CHARACTERISTICS

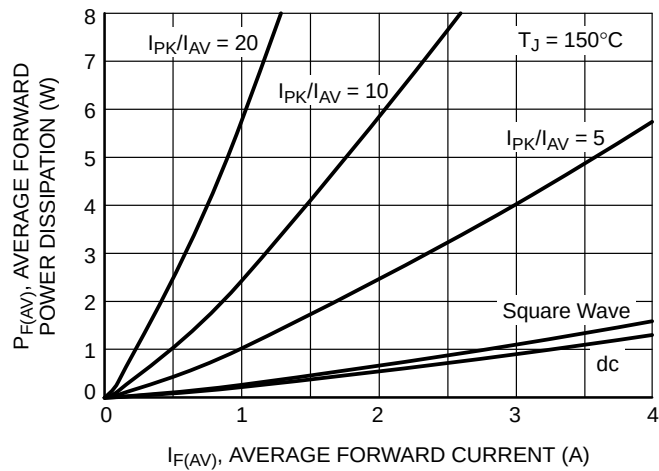


Figure 7. Forward Power Dissipation

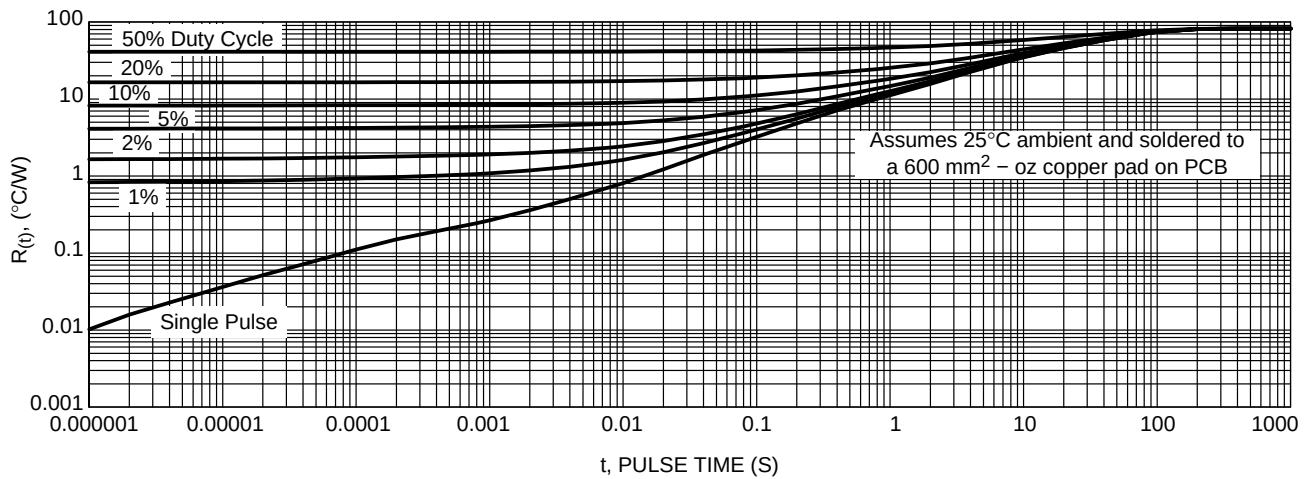


Figure 8. $R_{\theta(t)}$ vs. Duty

Данный компонент на территории Российской Федерации

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В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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